Complementary ThermalTrak[™] Transistors

The ThermalTrak family of devices has been designed to eliminate thermal equilibrium lag time and bias trimming in audio amplifier applications. They can also be used in other applications as transistor die protection devices.

Features

- Thermally Matched Bias Diode
- Instant Thermal Bias Tracking
- Absolute Thermal Integrity
- High Safe Operating Area
- Pb–Free Packages are Available*

Benefits

- Eliminates Thermal Equilibrium Lag Time and Bias Trimming
- Superior Sound Quality Through Improved Dynamic Temperature Response
- Significantly Improved Bias Stability
- Simplified Assembly
 - Reduced Labor Costs
 - Reduced Component Count
- High Reliability

Applications

- High-End Consumer Audio Products
 - Home Amplifiers
 - Home Receivers
- Professional Audio Amplifiers
 - Theater and Stadium Sound Systems
 - Public Address Systems (PAs)



ON Semiconductor®

http://onsemi.com

BIPOLAR POWER TRANSISTORS 15 AMP, 260 VOLT, 200 WATT

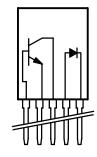


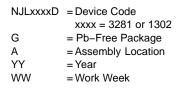
TO-264, 5 LEAD CASE 340AA STYLE 1

MARKING DIAGRAM

SCHEMATIC







ORDERING INFORMATION

Device	Package	Shipping
NJL3281D	TO-264	25 Units / Rail
NJL3281DG	TO-264 (Pb-Free)	25 Units / Rail
NJL1302D	TO-264	25 Units / Rail
NJL1302DG	TO–264 (Pb–Free)	25 Units / Rail

*For additional information on our Pb–Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

· 如何INUM 死在INGS ((社元东帝 unless otherwise noted)

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	260	Vdc
Collector-Base Voltage	V _{CBO}	260	Vdc
Emitter-Base Voltage	V _{EBO}	5	Vdc
Collector-Emitter Voltage - 1.5 V	V _{CEX}	260	Vdc
Collector Current – Continuous – Peak (Note 1)	Ι _C	15 25	Adc
Base Current – Continuous	ا _B	1.5	Adc
Total Power Dissipation @ $T_C = 25^{\circ}C$ Derate Above $25^{\circ}C$	PD	200 1.43	W ₩/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	- 65 to +150	°C
DC Blocking Voltage	V _R	200	V
Average Rectified Forward Current	I _{F(AV)}	V _R 200	

THERMAL CHARACTERISTICS

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction-to-Case	$R_{ extsf{ heta}JC}$	0.625	°C/W

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. Pulse Test: Pulse Width = 5 ms, Duty Cycle < 10%.

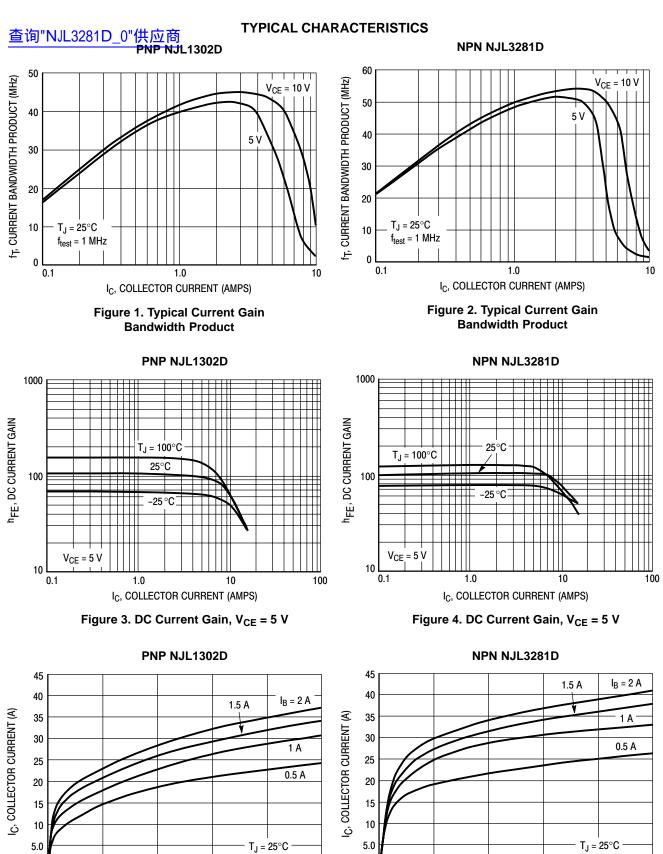
ATTRIBUTES

	Characteristic	Value
ESD Protection	Human Body Model Machine Model	>8000 V > 400 V
Flammability Rating		UL 94 V–0 @ 0.125 in

TICS (T_C = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Мах	Unit
OFF CHARACTERISTICS	·			
Collector–Emitter Sustaining Voltage $(I_C = 100 \text{ mAdc}, I_B = 0)$	V _{CEO(sus)}	260	_	Vdc
Collector Cutoff Current ($V_{CB} = 260 \text{ Vdc}, I_E = 0$)	I _{CBO}	-	50	μAdc
Emitter Cutoff Current ($V_{EB} = 5 Vdc, I_C = 0$)	I _{EBO}	-	5	μAdc
ON CHARACTERISTICS				
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 500 \text{ mAdc}, \text{ V}_{CE} = 5 \text{ Vdc}) \\ (I_{C} = 1 \text{ Adc}, \text{ V}_{CE} = 5 \text{ Vdc}) \\ (I_{C} = 3 \text{ Adc}, \text{ V}_{CE} = 5 \text{ Vdc}) \\ (I_{C} = 5 \text{ Adc}, \text{ V}_{CE} = 5 \text{ Vdc}) \\ (I_{C} = 8 \text{ Adc}, \text{ V}_{CE} = 5 \text{ Vdc}) \\ (I_{C} = 8 \text{ Adc}, \text{ V}_{CE} = 5 \text{ Vdc}) \end{array} $	h _{FE}	75 75 75 75 75 45	150 150 150 150 -	
Collector–Emitter Saturation Voltage $(I_C = 10 \text{ Adc}, I_B = 1 \text{ Adc})$	V _{CE(sat)}	-	3	Vdc
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product (I _C = 1 Adc, V _{CE} = 5 Vdc, f _{test} = 1 MHz)	f _T	30	_	MHz
Output Capacitance (V_{CB} = 10 Vdc, I _E = 0, f _{test} = 1 MHz)	C _{ob}	_	600	pF
Maximum Instantaneous Forward Voltage (Note 2) ($i_F = 1.0 \text{ A}, T_J = 25^{\circ}\text{C}$) ($i_F = 1.0 \text{ A}, T_J = 150^{\circ}\text{C}$)	۷F	1.1 0.93		V
Maximum Instantaneous Reverse Current (Note 2) (Rated dc Voltage, $T_J = 25^{\circ}C$) (Rated dc Voltage, $T_J = 150^{\circ}C$)	i _R		0 00	μΑ
Maximum Reverse Recovery Time (i _F = 1.0 A, di/dt = 50 A/μs)	t _{rr}	10	00	ns

2. Diode Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.



5.0

V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 6. Typical Output Characteristics

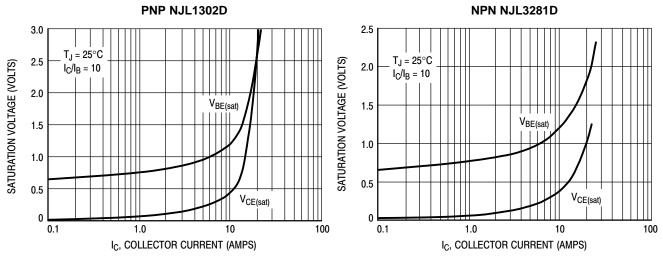
5.0

V_{CE}, COLLECTOR-EMITTER VOLTAGE (VOLTS)

Figure 5. Typical Output Characteristics

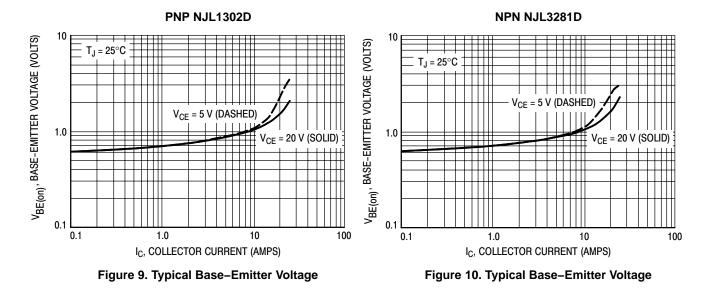
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TYPICAL CHARACTERISTICS



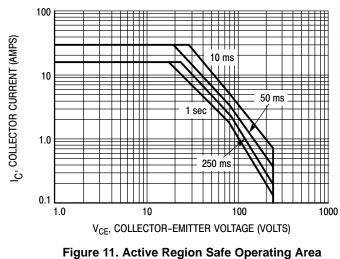






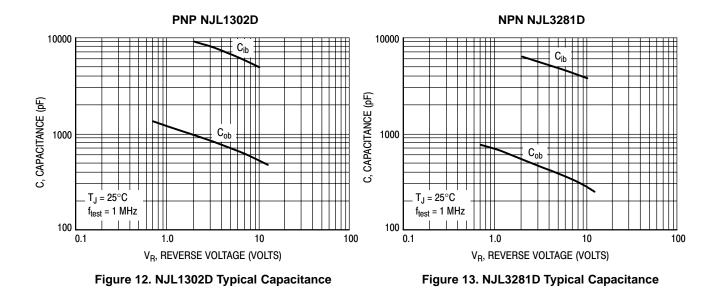
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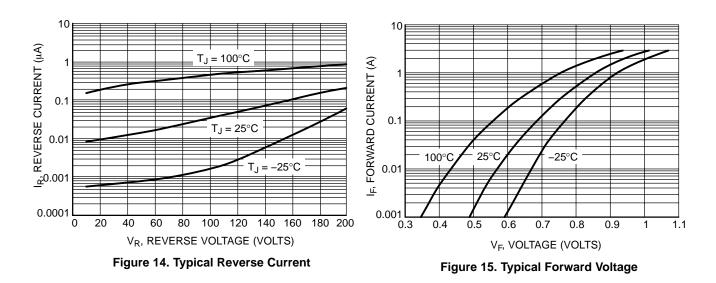
TYPICAL CHARACTERISTICS



There are two limitations on the power handling ability of a transistor; average junction temperature and secondary breakdown. Safe operating area curves indicate I_C - V_{CE} limits of the transistor that must be observed for reliable operation; i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 11 is based on $T_{J(pk)} = 150^{\circ}C$; T_C is variable depending on conditions. At high case temperatures, thermal limitations will reduce the power than can be handled to values less than the limitations imposed by second breakdown.



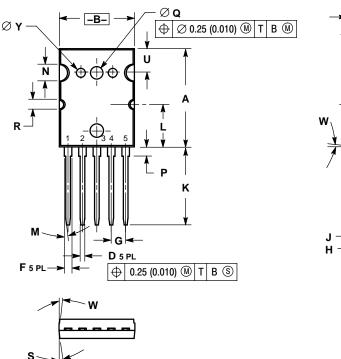


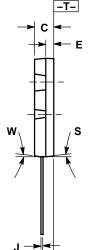
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PACKAGE DIMENSIONS

TO-264, 5 LEAD CASE 340AA-01 **ISSUE O**





ANSI Y14.5M, 1982. CONTROLLING DIMENSION: MILLIMETER.							
		LIMETE		INCHES			
DIM	MIN	NOM	MAX	MIN	NOM	MAX	
Α	25.857	25.984	26.111	1.018	1.023	1.028	
В	19.761	19.888	20.015	0.778	0.783	0.788	
С	4.928	5.055	5.182	0.194	0.199	0.204	
D	1.219 BSC		0.	0480 BS	SC		
Е	2.032	2.108	2.184	0.0800	0.0830	0.0860	
F	1.	981 BS(2	0.0780 BSC			
G	3	.81 BSC	;	0.150 BSC			
Н	2.667 2.718 2.769		0.1050	0.1070	0.1090		
J	0.584 BSC		SC .	0.0230 BSC			
κ	20.422	20.549	20.676	0.804	0.809	0.814	
L	11.28 REF		0.444 REF				
М	0 °		7 °	0 ° 7		7 °	
Ν		4.57 RE	F	0.180 REF			
Ρ	2.259	2.386	2.513	0.0889	0.0939	0.0989	
Q	3.480 BSC 2.54 REF		C	.1370 B	SC		
R			0.100 REF				
S	0 °		8 °	0 °		8 °	
U	6.17 REF			0.243 R			
w	0 °		6 °	0 °		6 °	
Y	2.388 BSC			C	.0940 B	SC	

DIMENSIONING AND TOLERANCING PER

STYLE 1:

NOTES

PIN 1. BASE 2. EMITTER 3. COLLECTOR 4. ANODE

5. CATHODE

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